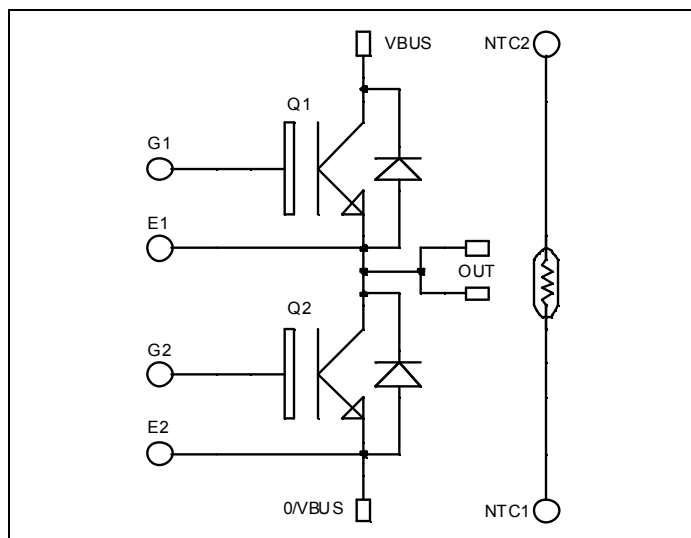


Phase leg NPT IGBT Power Module

$V_{CES} = 1200V$
 $I_C = 150A @ T_c = 80^\circ C$

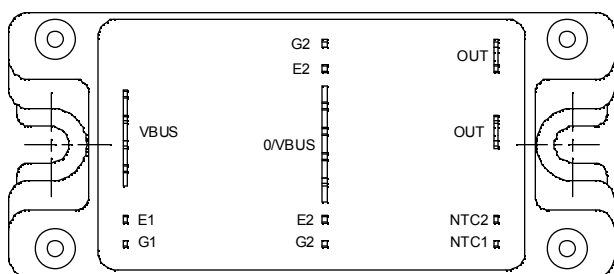


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Non Punch Through (NPT) Fast IGBT®
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 50 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - Avalanche energy rated
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration



Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage	1200	V
I_C	Continuous Collector Current	$T_c = 25^\circ C$	A
		$T_c = 80^\circ C$	
I_{CM}	Pulsed Collector Current	$T_c = 25^\circ C$	300
V_{GE}	Gate - Emitter Voltage	± 20	V
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	961
RBSOA	Reverse Bias Safe Operating Area	$T_j = 150^\circ C$	300A @ 1200V

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0\text{V}$ $V_{CE} = 1200\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			350 600	μA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15\text{V}$ $I_C = 150\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		3.2 3.9	3.7	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 5\text{mA}$		4.5		6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}$				± 500	nA

Dynamic Characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
C_{ies}	Input Capacitance	$V_{GE} = 0\text{V}$ $V_{CE} = 25\text{V}$ $f = 1\text{MHz}$			10.2		nF
C_{oes}	Output Capacitance				1.4		
C_{res}	Reverse Transfer Capacitance				0.75		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$			120		ns
T_r	Rise Time				50		
$T_{d(off)}$	Turn-off Delay Time				310		
T_f	Fall Time				20		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C) $V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$			130		ns
T_r	Rise Time				60		
$T_{d(off)}$	Turn-off Delay Time				360		
T_f	Fall Time				30		
E_{on}	Turn-on Switching Energy	$V_{GE} = 15\text{V}$ $V_{Bus} = 600\text{V}$ $I_C = 150\text{A}$ $R_G = 5.6\Omega$	$T_j = 125^\circ\text{C}$		18		mJ
E_{off}	Turn-off Switching Energy		$T_j = 125^\circ\text{C}$		8		

Reverse diode ratings and characteristics

<i>Symbol</i>	<i>Characteristic</i>	<i>Test Conditions</i>		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1200			V
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			500 750	μA
I_F	DC Forward Current		$T_c = 80^\circ\text{C}$		100		A
V_F	Diode Forward Voltage	$I_F = 100\text{A}$	$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		2.1 1.9		V
t_{rr}	Reverse Recovery Time	$I_F = 100\text{A}$ $V_R = 600\text{V}$ $di/dt = 2500\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		95		ns
			$T_j = 125^\circ\text{C}$		190		
Q_{rr}	Reverse Recovery Charge		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		8.4 18		μC
E_r	Reverse Recovery Energy		$T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$		3 6		mJ

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

Symbol Characteristic

Min Typ Max Unit

R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
R_T: Thermistor value at T

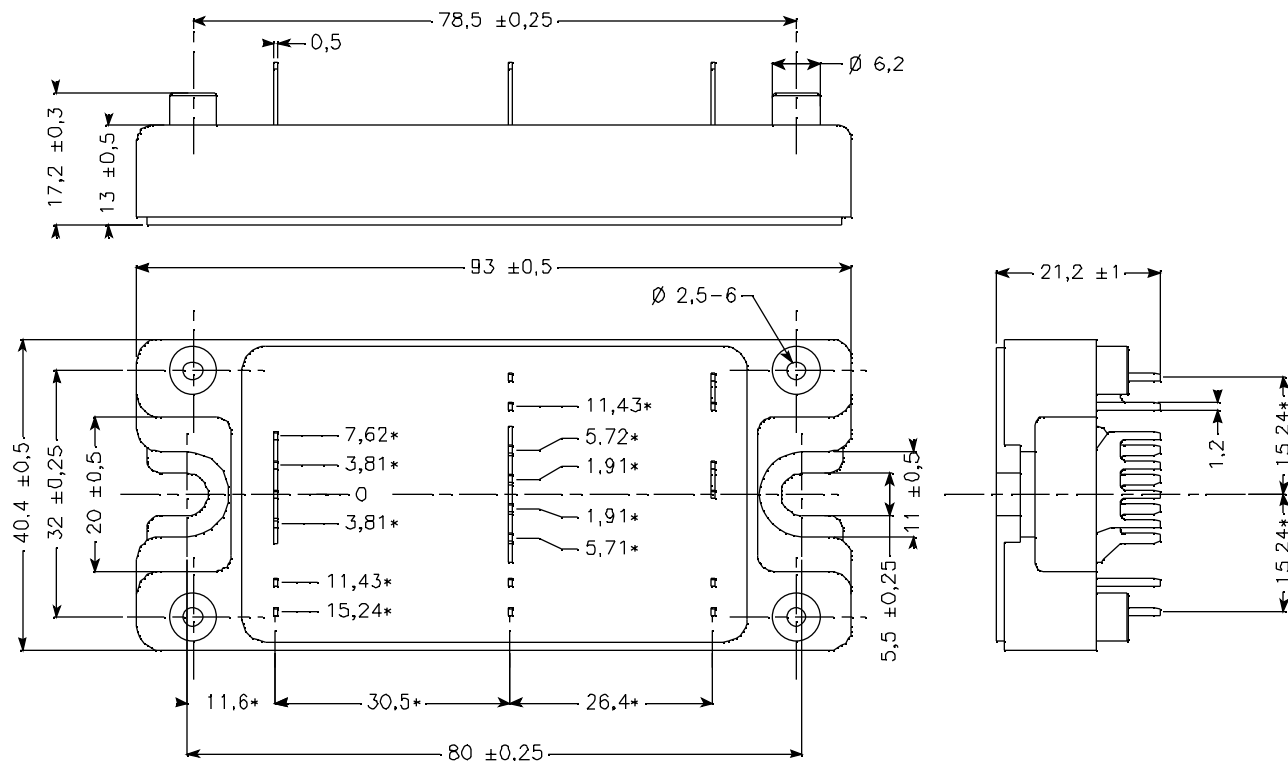
Thermal and package characteristics

Symbol Characteristic

Min Typ Max Unit

R _{thJC}	Junction to Case Thermal Resistance	IGBT			0.13	°C/W
		Diode			0.32	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t = 1 min, I _{isol} < 1mA, 50/60Hz	2500				V
T _J	Operating junction temperature range	-40		150		°C
T _{STG}	Storage Temperature Range	-40		125		
T _C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M5	2.5	4.7	N.m
Wt	Package Weight				160	g

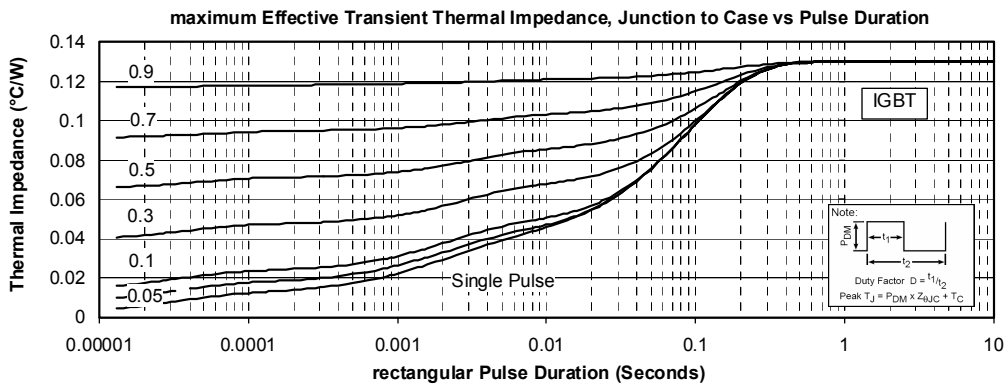
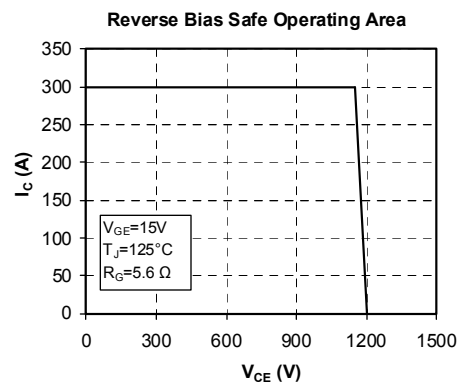
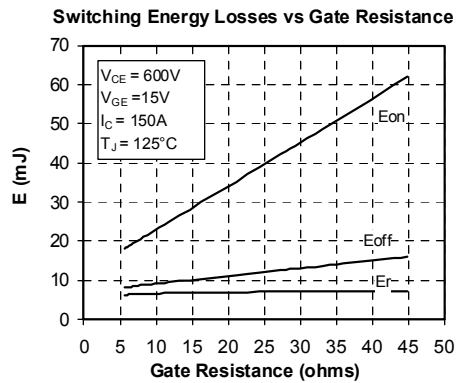
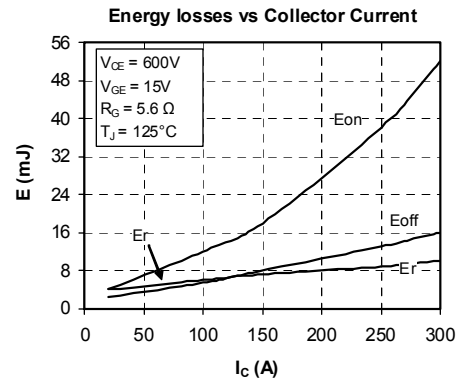
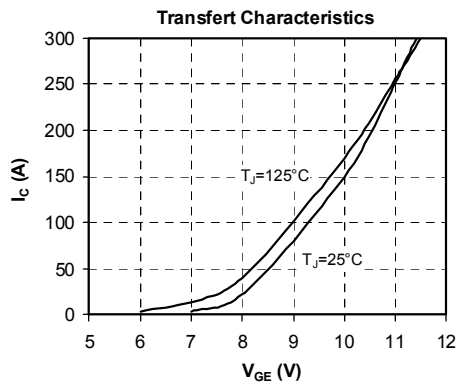
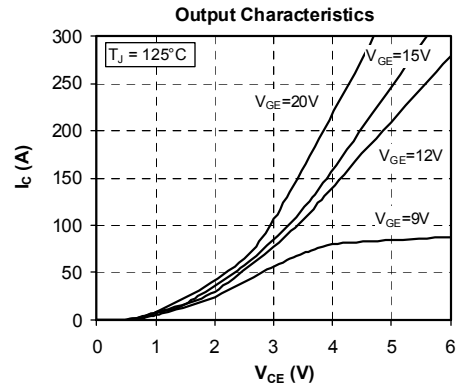
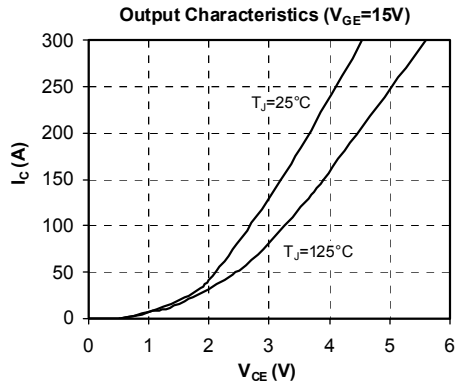
SP4 Package outline (dimensions in mm)

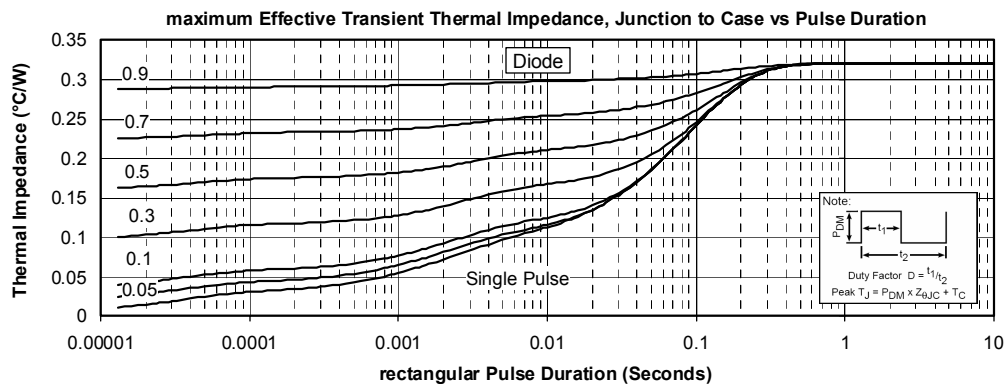
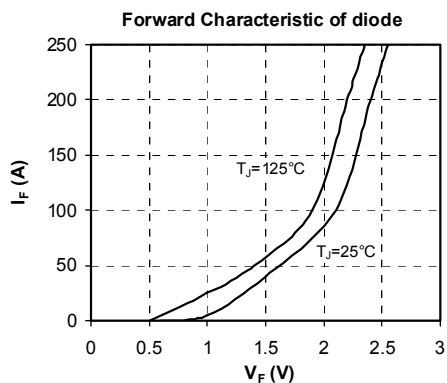
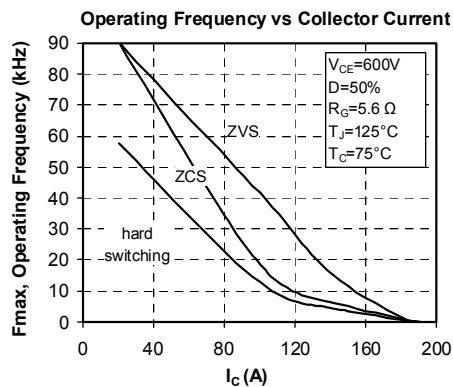


ALL DIMENSIONS MARKED "*" ARE TOLERENCED AS: ± 0.1

See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

Typical Performance Curve





Microsemi reserves the right to change, without notice, the specifications and information contained herein

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